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"Correlated" bands in oxides with wave-function based methods

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1 Goals and approach

• "correlated" bands in oxides, wave-function based methodology

2 First applications

• MgO, a prototype closed-shell ionic insulator

Preliminary results for TM oxides

• renormalized bands and Fermiology in layered Cu oxides

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- compute energy bands with quantum chemical accuracy
- long-term objective: strong correlations in transition-metal compounds — magnetism, satellite structures etc.

Motivation

 the limitations of the DFT-based methods:
 band gaps, "strong correlations" in 3d and 4f solid-state compounds (Mott insulating states, magnetism etc.)

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quasiparticle picture, local Hamiltonian formalism

first step: all-electron Hartree-Fock calc. for the *periodic system* → HF bands, localized Wannier orbitals (WO's) [CRYSTAL program]

second step: the correlation treatment [MOLPRO package]

- *finite fragment C* cut from the infinite solid (up to 100 sites, to include the tails of the "active" orbitals)
- use the data from the periodic Hartree-Fock (HF) calculation
 - localized WO's at the atomic sites of the finite cluster
 - HF embedding potential due to the rest of the crystal (the surrounding HF electron "sea")

 $V_{\alpha\beta}^{\text{emb}} = F_{\alpha\beta}^{\text{crys}} - F[P_{\mathcal{C}}]_{\alpha\beta}, \quad P_{\mathcal{C}} = 2\sum_{\nu}^{\text{occ}} |w_{\nu}\rangle \langle w_{\nu}|, \quad \alpha, \beta, \nu \in \mathcal{C}$

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Starting point: Hartree-Fock

The fundamental gap: (N+1)/(N-1) el. addition/removal states

 $|\Phi_{\mathbf{R}c\sigma}^{N+1}\rangle = c_{\mathbf{R}c\sigma}^{\dagger}|\Phi\rangle$ and $|\Phi_{\mathbf{R}v\sigma}^{N-1}\rangle = c_{\mathbf{R}v\sigma}|\Phi\rangle$

For <u>clusters</u> which are large enough, the HF bands of the periodic crystal can be recovered by diagonalizing \mathbf{k} -dependent matrices of the form:

$$H_{nn'}^{\rm HF}(\mathbf{k}) = \sum_{\mathbf{R}} e^{i\mathbf{k}\mathbf{R}} \left(\langle \Phi_{\mathbf{0}n\sigma}^{N\mp1} | H | \Phi_{\mathbf{R}n'\sigma}^{N\mp1} \rangle - E_0^{\rm HF} \delta_{\mathbf{0}\mathbf{R}} \delta_{nn'} \right)$$

Diagonal terms (R=0): on-site Koopmans excitation energies, i.e., ionization potentials $IP_{vv}^{HF}(\mathbf{0}) = \langle \Phi_{\mathbf{0}v\sigma}^{N-1} | H | \Phi_{\mathbf{0}v\sigma}^{N-1} \rangle - E_0^{HF} = -\epsilon_{\mathbf{0}v}^{HF} > 0$ and electron affinities $EA_{cc}^{HF}(\mathbf{0}) = E_0^{HF} - \langle \Phi_{\mathbf{0}c\sigma}^{N+1} | H | \Phi_{\mathbf{0}c\sigma}^{N+1} \rangle = -\epsilon_{\mathbf{0}c}^{HF} < 0$

Off-diagonal (R \neq 0): tight-binding hopping matrix elements (ME's) $t_{nn'}^{\text{HF}}(\mathbf{R}) = \langle \Phi_{\mathbf{0}n\sigma}^{N\mp1} | H - E_0^{\text{HF}} | \Phi_{\mathbf{R}n'\sigma}^{N\mp1} \rangle$



Short-range relaxation and polarization: separate SCF optimizations, orbitals in the immediate neighborhood of the additional electron (hole) [the $(N\pm 1)$ Wannier orbital is kept frozen]

Loss of ground-state correlations: small effect, not discussed here

Long-range polarization :

the approximation of a dielectric continuum

$$\Delta E(\infty) = \Delta E(R_i) - C/R_i , \quad C = rac{\epsilon_0 - 1}{2\epsilon_0}e^2$$

C: by computing $\Delta E(R_1)$, $\Delta E(R_2)$ for two different radii R_1 , R_2

 \longmapsto "correlated" wave-functions, renormalized real-space ME's:

$$H_{nn'}(\mathbf{k}) = \sum_{\mathbf{R}} e^{i\mathbf{k}\mathbf{R}} \left(\langle \Psi_{\mathbf{0}n\sigma}^{N\mp1} | H | \Psi_{\mathbf{R}n'\sigma}^{N\mp1} \rangle - E_{\mathbf{0}} \delta_{\mathbf{0}\mathbf{R}} \delta_{nn'} \right)$$

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MgO: the HF data



- HF gap: 16.20 eV; Exp.: 7.8 eV (Basis sets: Mg - TZ; O - TZ + pol.)
- low-lying conduction bands: Mg 3s-3p
- valence-band states : oxygen 2p

Conduction-band Wannier orbitals (WO's):

 ${\ensuremath{\bullet}}$ the most diffuse

after projection onto the finite cluster, their norms are >98.5% of the orig. WO's





Short-range relaxation and polarization effects

- separate SCF optimizations, orbitals in the immediate neighborhood of the additional electron/hole
- the "(N±1)" th Wannier orbital is frozen



$\Delta H_{nn}(0)$	0 2 <i>s</i>	0 2 <i>p</i>	Mg 3 <i>s</i>	Mg 3p	
On-site orb. relaxation	-2.64	-2.04	—	_	
NN orb. relaxation	-1.23	-1.20	-0.81	-0.84	
NNN orb. relaxation	-0.18	-0.18			
$(O_{2a}/2\pi) MO'_{ab} 12 NN$	0'	1 m 2 m /2 m		0'-	£: .

(O 2s/2p WO's: <u>12 NN O's</u>; Mg 3s/3p WO's: <u>6 NN O's</u>, see figure)

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Long-range polarization

The approximation of a *dielectric continuum*:

 $\Delta E(\infty) = \Delta E(R_i) - C/R_i$

• $\Delta E(R_i)$: short-range relax./pol. within a sphere of radius R_i

• C: a)
$$C = \frac{\epsilon_0 - 1}{2\epsilon_0} e^2 \longrightarrow C = 0.45 \text{ a.u.} (\epsilon_0 = 9.7)$$

b) by computing $\delta E_{ji} = \Delta E(R_j) - \Delta E(R_i)$
 $R_i : \text{NN's}; R_j : \text{NN's} + \text{NNN's} (previous page)$
 $C \sim \frac{R_i R_j}{R_j - R_i} \delta E_{ji} \longrightarrow C = 0.41 \text{ a.u.}$

 $\longrightarrow \,$ the approx. of a dielectric continuum works quite well

$\Delta H_{nn}(0)$	0 2 <i>s</i>	0 2 <i>p</i>	Mg 3 <i>s</i>	Mg 3 <i>p</i>
Long-range polarization	-1.80	-1.80	-2.25	-2.25

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Correlation-induced corrections to the gap

$\Delta H_{nn}(0)$	0 2 <i>s</i>	O 2 <i>p</i>	Mg 3 <i>s</i>	Mg 3 <i>p</i>
On-site orb. relaxation	-2.64	-2.04	—	—
NN orb. relaxation	-1.23	-1.20	-0.81	-0.84
Long-range polarization	-1.80	-1.80	-2.25	-2.25
Total	-5.67	-5.04	-3.06	-3.09

- valence bands: shift *upwards* by approx. 5 eV
- conduction bands: downwards shift, approx. 3.1 eV
- "correlated" gap: 8.1 eV; exp.: 7.8 eV
- LDA gap: 5.0 eV [CRYSTAL package]

95% of the difference between HF and experiment !!

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Renormalized hoppings, band widths

less affected, as compared to the diagonal (on-site) matrix elements

- separately optimized $(N \pm 1)$ wave-functions $\Psi_{0i}^{N\pm 1}$, $\Psi_{Rj}^{N\pm 1}$ (relaxation effects in the immediate vicinity of the extra particle)
- t_{ij} = (H_{ij} − S_{ij}H_{ii})/(1 − S²_{ij}) [2×2 secular problem in terms of non-orthog. sets of orbitals (Non-Orthog. Config.-Interaction, <u>NOCI</u>)]





Conduction-band hopping matrix elements

Conduction-band states (Mg 3s-3p): changes within $\sim 5\%$

$t_{ij}(\mathbf{R})$	HF (frozen orb. CI)	NOCI (relaxed orbs.)
t _{NN} :		
3 <i>s</i> – 3 <i>s</i>	0.41	0.42
$3p_{x(y)} - 3p_{x(y)}$	0.66	0.69
$3p_{x(y)} - 3p_{y(x)}$	0.72	0.77
$3p_{z} - 3p_{z}$	0.13	0.13
t _{NNN} :		
3 <i>s</i> – 3 <i>s</i>	0.36	0.37
$3p_x - 3p_x$	0.77	0.74
$3p_{y(z)} - 3p_{y(z)}$	0.13	0.12

• some hoppings are enlarged, some are reduced by correlations

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 $\bullet\,$ correlation-induced broadening, by $\,10-15\%$

$t_{ii}(\mathbf{R})$	HF (FO-CI)	NOCI (relaxed orbitals)	
	. ,	Two-site	Two-site, NN O's
t _{NN} :			
$2p_{x(y)} - 2p_{y(x)}$	0.42	0.49	0.47
$2p_{x(y)} - 2p_{x(y)}$	0.32	0.37	0.36
$2p_z - 2p_z$	0.12	0.14	0.13
t _{NNN} :			
$2p_{x} - 2p_{x} (\sigma$ -ov.)	0.06	0.06	—

- main effect :
 "bending" of the p orbitals due to the adjacent O hole → increased inter-site overlap
- $w_{2p}^{\Gamma L} = 8t_{xx}^{110} + 8t_{xy}^{110} 4t_{xx}^{011} + ...$ $w_{2p}^{\Gamma L}$: 5.5 (HF) \longrightarrow 6.2 (HF + correl.)



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O valence bands: comparison to experiment

	HF	HF + correl.	PES	LDA
(0)		C D		47
w(2p)	5.5	6.2	\sim 6.5 [1,2]	4.7
$\Delta E_{2p}^{1,2}$	3.5		3.5 [2]	3.0
ΔE_{2s2p}	15.9	14.8	14.0 [1]	10.7

[1] S. Kowalczyk, D. A. Shirley et al., Solid State Commun. 23 (1977). [2] L. H. Tjeng et al., Surf. Sci. 235 (1990).

- $\Delta E_{2p}^{1,2}$: separation between the two O 2p peaks
- ΔE_{2s2p} : O 2s bottom of the 2p bands



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MgO:

- charge relaxation effects are essential for computing accurate band gaps
- band widths are less affected

What about spin polarization and relaxation ?

Illustrative example :

doped hole (electron) in the cuprate antiferromagnetic lattice (reduction by a factor of 4 of the band widths)

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"Correlated" bands in layered Cu oxides

Formal valence states for the undoped layer:



Superconductivity: both *hole* and *electron* doping (e.g., $La_{2-x}Sr_xCuO_4$ vs. $Sr_{1-x}Nd_xCuO_2$)

Dressed carriers: strong correlation effects (charge, spin, ...)

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Ab initio wave-function based approach

Finite fragments (up to 11 CuO₄ plaquettes): all-electron, multiconfiguration calculations [MOLCAS package]

(Static) embedding:

- Madelung field ← point charges
- finite charge distrib. of NN's ← effective ion potentials

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less rigorous as compared to the study on MgO

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Multiconfiguration approach : CAS SCF

The minimal active space in cuprates : one $3d_{x^2-y^2}$ orbital per Cu site

• provides the correct antiferromagnetic (AFM) ground-state configuration (*Anderson superexchange mechanism*)

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Multiconfiguration approach : CAS SCF

The *N*-electron wave-function : complete active space (CAS) "full" Configuration Interaction (CI) within a relatively small set of <u>"active" orbitals</u> (e.g., one $3d_{x^2-y^2}$ per Cu site) $\longrightarrow \Psi = \sum_{k}^{CAS} C_k \Phi_k$



• highly flexible: orbitals and Cl coefficients are both variationally optimized

 near-degeneracy (static) correlation effects: competing valence structures, bond breaking, <u>magnetism</u> (Anderson superexchange, double exchange) etc.

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The Zhang-Rice (ZR) -like state



An O 2*p*, ZR-like hole induces *ferromagnetic correlations* among the *adjacent* Cu $d_{x^2-y^2}$ spins: FM "spin polaron"

Relevant AOs	Mulliken charge	Mulliken spin
$Cu_c \; 3d_{x^2-y^2}$	1.17	0.06
$O_c^{x,y}$ 2 $p_{x,y}$	1.62	-0.01
$Cu_{nn}^{x,y} 3d_{x^2-y^2}$	1.27	0.31
$Cu_{nnn}^{xy} 3d_{x^2-y^2}$	1.28	-0.32

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Nonlocal spin correlations, effective hoppings



Effective hoppings (QP picture): $t = (H_{LR} - S_{LR}H_{LL})/(1 - S_{LR}^2)$ $H_{LR} = \langle \Psi_L | H | \Psi_R \rangle$, $S_{LR} = \langle \Psi_L | \Psi_R \rangle$

 Ψ_L , Ψ_R : separately optimized, localized ZR-like solutions (CASSCF) \longrightarrow both charge and <u>spin</u> relaxation ("readjustment") on neighboring plaquettes

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Renormalized hoppings

When moving through the AFM lattice, the O 2p hole must drag along the spin polarization "cloud" at nearby Cu sites \longrightarrow strong renormalization of the hoppings (essentially, non-dynamical correlation)

CASSCF and State-Interaction (CAS SI) calculations :

 ${\ensuremath{\bullet}}$ 2(3)-plaquette "central" region (L,R) $\ +$ adjacent plaquettes

• "bare" t: a) the Cu²⁺ $3d^9$ (S = 1/2) neighbors \longrightarrow Zn²⁺ $3d^{10}$ (S = 0) b) FM "lattice"



	Bare values	Renorm.
t	0.450/0.540	0.133
ť	0.262/0.305	0.014
t″	0.107/0.113	0.073

[LDA: $t \approx 0.45$ eV; Fits of PES data: $t \approx 0.15$]

Tight-binding dispersion $\epsilon(\mathbf{k})$: $-2t(\cos k_x + \cos k_y) + 4t' \cos k_x \cos k_y$ $-2t''(\cos 2k_x + \cos 2k_y) + ...$

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The ZR-like band



All important details of the experimental spectrum are faithfully reproduced in the theoretical results:

- overall width of $\approx\!1~\text{eV}$
- flat dispersion near the $(\pi, 0)$ point
- maximum close to the $(\pi/2,\pi/2)$ region



States at higher binding energies: z^2 holes

Significant nearest-neighbor mixing between the ZR-like and z² hole states: t_m(cos k_x - cos k_y); t_m = 0.15, Δε = 0.60 (eV) [CASSCF/State-Interaction (CAS SI)]

Mulliken charge	$d_{x^2-y^2}$	$d_{3z^2 - r^2}$	$\sigma p_x/p_y$ (x4)	apex p_z
ZR hole	1.05	2.00	1.60	1.95
$d_{3z^2-r^2}$ hole	1.40	1.15	1.70	1.85

Undoped system, Mulliken charges of the $\sigma p_x/p_y$ O orbitals: ≈ 1.85



- Dashed line: ZR dispersion
- <u>Full line</u>: lowest renormalized electron-removal band including the ZR-z² mixing

- Dots: t'' = 0
- <u>Experiment</u>: AR-PES, Ino et al., PRB **62** (2000).

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Fermi "surface": doping dependence

- Undoped cuprates: Mott insulators
- With doping: uniform shift of the Fermi level across the valence/conduction bands (ARPES, core-level XPS, optical absorption); *rigid-band picture*

The evolution of the FS with (hole) doping, as seen in ARPES and magneto-transport measurements, follows directly from our ab initio results :



- deeply underdoped regime : small hole pockets around (π/2,π/2); d-wave "pseudogap"
- intermediate doping : hole-like FS; d-wave pseudogap
- overdoped region : gapless electron-like FS

New insight into the nature of the pseudogap state ! (no need to invoke exotic mechanisms such as charge "stripes")

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Electron doped cuprates

- ARPES measurements [Armitage et al., PRL 88 (2000)]:



- CASSCF/SI: in a rigid-band picture, confirm the ARPES data



- low (electron) doping → small pockets at (π,0)
- larger dopings → hole-like FS, d-wave pseudogap

 $(3d^{10}$ "QP" on the $3d^9$ "lattice"; compared to the ZR band, different ratios among the effect. hoppings)

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Conclu	usions			

- transparent formalism, *controlled* approximations
- For MgO, a simple closed-shell ionic insulator :
 - good <u>understanding</u> of the major effects that determine the electronic band structure
 - good agreement with the experiment
- Next: dressed carriers in strongly correlated Cu oxides
 - renormalized hoppings of the ZR-like quasiparticle, not accessible by DFT
 - ZR physics : richer than in the t-J picture
 - reproduce and explain the ARPES data (quasiparticle dispersion, topology of the Fermi surface)

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[PRB 76, 085109 (2007); PRB 75, 174505 (2007); cond-mat:0707.4648]